

# OPA355-Q1 200MHz CMOS 运算放大器，具有关断功能

## 1 特性

- 符合汽车类应用的要求
- 具有符合 AEC-Q100 标准的下列特性
  - 器件温度 1 级: -40°C 至 +125°C 的环境运行温度范围
  - 器件 HBM ESD 分类等级 2
  - 器件 CDM ESD 分类等级 C4B
- 单位增益带宽: 450MHz
- 宽带宽: 200MHz GBW
- 高转换率: 360V/μs
- 低噪声: 5.8 nV/√Hz
- 出色的视频性能:
  - 差分增益: 0.02%
  - 差分相位: 0.05° (0.1dB)
  - 增益平坦度: 75MHz
- 输入范围包括接地
- 轨至轨输出 (在 100mV 以内)
- 低输入偏置电流: 3pA
- 低关断电流: 3.4μA
- 启用和禁用时间: 100ns 和 30ns
- 热关断
- 单电源工作电压范围: 2.5V 至 5.5V
- MicroSIZE 封装

## 2 应用

- 汽车
- 有源滤波器
- 高速积分器
- 模数转换器 (ADC) 输入缓冲器
- 数模转换器 (DAC) 输出放大器

## 3 说明

OPA355-Q1 器件是一款高速电压反馈 CMOS 运算放大器，专为需要宽带宽的应用而设计。OPA355-Q1 器件单位增益稳定并且可驱动大输出电流。此外，OPA355-Q1 器件具有一个数字关断 (使能) 功能。这个特性在空闲期间提供节电功能，并将输出置于高阻抗状态，以支持输出复用。差分增益为 0.02%，而差分相位为 0.05°。每通道的静态电流为 8.3mA。

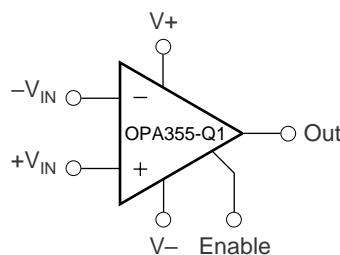
OPA355-Q1 针对低至 2.5V ( $\pm 1.25V$ ) 和高达 5.5V ( $\pm 2.75V$ ) 的单电源或双电源供电运行进行了优化。针对 OPA355-Q1 器件的共模输入范围扩展至低于接地电压 100mV 以下和高达 V+ 以上 1.5V。电源轨的输出摆幅在 100mV 以内，从而支持宽动态范围。

OPA355-Q1 器件采用单 SOT-23-6 封装，具有 -40°C 至 +125°C 的扩展温度范围。

### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
OPA355-Q1	SOT-23 (6)	2.90mm × 1.60mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品目录。



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## 4 修订历史记录

## Changes from Revision B (June 2014) to Revision C

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•	Deleted "C55" marking on pinout drawing in <i>Pin Configuration and Functions</i> section .....	3
•	Added Pin Functions table to <i>Pin Configuration and Functions</i> section .....	3
•	Deleted storage temperature range from <i>ESD Ratings</i> table and moved to <i>Absolute Maximum Ratings</i> table .....	4
•	Changed title of <i>Handling Ratings</i> table to <i>ESD Ratings</i> table .....	4
•	Added <i>Recommended Operating Conditions</i> table .....	4
•	已添加 <i>Functional Block Diagram</i> .....	12
•	已删除 "Independent enable pins are available for each channel, which provide maximum design flexibility" from <i>Enable Function</i> section .....	12
•	已删除 <i>Input and ESD Protection</i> subsection in <i>Feature Description</i> section .....	13
•	已添加 <i>Device Functional Modes</i> section .....	13
•	已添加 <i>Typical Applications</i> section to <i>Application and Implementation</i> section .....	14
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•	已添加 <i>High-Impedance Sensor Interface, Driving ADCs, and Active Filter</i> subsections to <i>Typical Application</i> section ....	16
•	已添加 <i>Power Supply Recommendations</i> section .....	19
•	已添加 layout example image to <i>Layout</i> section .....	19

## Changes from Revision A (December 2013) to Revision B

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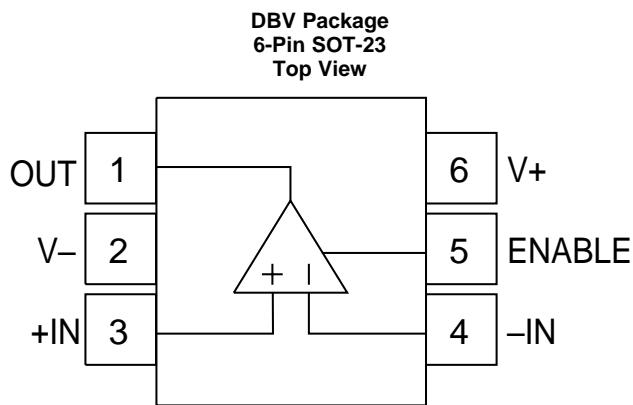
•	已更改 器件状态从 产品预览 更改为 量产数据 .....	1
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## 5 Device Comparison Table

### 5.1 Device Comparison Table

OPA355-Q1 RELATED PRODUCTS	FEATURES
OPA356	200-MHz, Rail-to-Rail Output, CMOS, No Shutdown
OPAx350	38-MHz, Rail-to-Rail Input and Output, CMOS
OPAx631	75-MHz, Rail-to-Rail Output
OPAx634	150-MHz, Rail-to-Rail Output
THS412x	Differential Input and Output, 3.3-V Supply

## 6 Pin Configuration and Functions



Pin 1 of the SOT-23-6 is determined by orienting the package marking as indicated in the diagram.

**Pin Functions**

PIN		I/O	DESCRIPTION
NAME	NO.		
ENABLE	5	—	Amplifier power down. Low = disabled, high = normal operation (pin must be driven) .
IN+	3	I	Noninverting input pin
IN-	4	I	Inverting input pin
OUT	1	O	Output pin
V+	6	—	Positive power supply
V-	2	—	Negative power supply

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Supply voltage	V+ to V-		7.5	V
Signal input terminals	Voltage	(V-) - 0.5	(V+) + 0.5	V
	Current		10	mA
Output short circuit <sup>(2)</sup>	Continuous			
Operating temperature		-55	150	°C
Junction temperature			160	°C
Lead temperature (soldering, 10 seconds)			300	°C
Storage temperature range, T <sub>stg</sub>		-65	150	°C

- (1) Stresses above *Absolute Maximum Ratings* may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) Short-circuit to ground, one amplifier per package.

### 7.2 ESD Ratings

		MIN	MAX	UNIT
V <sub>(ESD)</sub>	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>		2000	V
	Charged device model (CDM), per AEC Q100-011	Corner pins (1, 3, 4, and 6)	750	
		Other pins	500	

- (1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
V <sub>S</sub> Total supply voltage	2.7		5.5	V
T <sub>A</sub> Ambient temperature	-40	25	125	°C

### 7.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		OPA355-Q1	UNIT
		DBV (SOT-23)	
		6 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	187.3	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	126.5	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	32.6	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	24.1	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	32.1	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 7.5 Electrical Characteristics

$V_S = 2.7 \text{ V}$  to  $5.5 \text{ V}$  (single-supply). At  $T_A = 25^\circ\text{C}$ ,  $R_F = 604 \Omega$ ,  $R_L = 150 \Omega$ , and connected to  $V_S / 2$ , (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT			
<b>OFFSET VOLTAGE</b>										
$V_{OS}$	Input offset voltage	$V_S = 5 \text{ V}$	$T_A = 25^\circ\text{C}$	$\pm 2$	$\pm 9$	$\pm 15$	mV			
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
$\frac{DV_{OS}}{dT}$	Input offset voltage vs temperature	$T_A = 25^\circ\text{C}$		$\pm 7$	$\mu\text{V}/^\circ\text{C}$	$\pm 7$	$\mu\text{V}/^\circ\text{C}$			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
$PSRR$	Input offset voltage vs power supply	$V_S = 2.7$ to $5.5 \text{ V}$ ,	$T_A = 25^\circ\text{C}$	$\pm 80$	$\pm 350$	$\pm 350$	$\mu\text{V}/\text{V}$			
		$V_{CM} = V_S / 2 - 0.15 \text{ V}$	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
<b>INPUT BIAS CURRENT</b>										
$I_B$	Input bias current	$T_A = 25^\circ\text{C}$		3	$\pm 50$	$\pm 50$	pA			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
$I_{OS}$	Input offset current	$T_A = 25^\circ\text{C}$		$\pm 1$	$\pm 1$	$\pm 1$	pA			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
<b>NOISE</b>										
$e_n$	Input noise voltage density	$f = 1 \text{ MHz}$	$T_A = 25^\circ\text{C}$	5.8	$\text{nV}/\sqrt{\text{Hz}}$	$\text{nV}/\sqrt{\text{Hz}}$	$\text{nV}/\sqrt{\text{Hz}}$			
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
$i_n$	Current noise density	$f = 1 \text{ MHz}$	$T_A = 25^\circ\text{C}$	50	$\text{fA}/\sqrt{\text{Hz}}$	$\text{fA}/\sqrt{\text{Hz}}$	$\text{fA}/\sqrt{\text{Hz}}$			
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
<b>INPUT VOLTAGE RANGE</b>										
$V_{CM}$	Common-mode voltage range	$T_A = 25^\circ\text{C}$		$(V-) - 0.1$	$(V+) - 1.5$	$(V+) - 1.5$	V			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
$CMRR$	Common-mode rejection ratio	$V_S = 5.5 \text{ V}$ $-0.1 \text{ V} < V_{CM} < 4 \text{ V}$	$T_A = 25^\circ\text{C}$	66	80	66	dB			
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
<b>INPUT IMPEDANCE</b>										
	Differential	$T_A = 25^\circ\text{C}$		$10^{13} \parallel 1.5$		$\Omega \parallel \text{pF}$	$\Omega \parallel \text{pF}$			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
	Common-mode	$T_A = 25^\circ\text{C}$		$10^{13} \parallel 1.5$		$\Omega \parallel \text{pF}$	$\Omega \parallel \text{pF}$			
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$								
<b>OPEN-LOOP GAIN</b>										
	Open-loop gain	$V_S = 5 \text{ V}$ $0.3 \text{ V} < V_O < 4.7 \text{ V}$	$T_A = 25^\circ\text{C}$	84	92	80	dB			
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$							
<b>FREQUENCY RESPONSE</b>										
$f_{-3\text{dB}}$	Small-signal bandwidth	$G = 1$ , $V_O = 100 \text{ mVp-p}$ , $R_F = 0 \Omega$ , $T_A = 25^\circ\text{C}$		450		MHz	MHz			
		$G = 2$ , $V_O = 100 \text{ mVp-p}$ , $R_L = 50 \Omega$ , $T_A = 25^\circ\text{C}$		100						
		$G = 2$ , $V_O = 100 \text{ mVp-p}$ , $R_L = 150 \Omega$ , $T_A = 25^\circ\text{C}$		170						
		$G = 2$ , $V_O = 100 \text{ mVp-p}$ , $R_L = 1 \text{ k}\Omega$ , $T_A = 25^\circ\text{C}$		200						
GBW	Gain-bandwidth product	$G = 10$ , $R_L = 1 \text{ k}\Omega$ , $T_A = 25^\circ\text{C}$		200		MHz				
$f_{0.1 \text{ dB}}$	Bandwidth for 0.1-db gain flatness	$G = 2$ , $V_O = 100 \text{ mVp-p}$ , $R_F = 560 \Omega$ , $T_A = 25^\circ\text{C}$		75		MHz				
SR	Slew rate	$V_S = 5 \text{ V}$ , $G = 2$ , 4-V output step, $T_A = 25^\circ\text{C}$		300 / -360		V/ $\mu$ s				
	Rise and fall time	$G = 2$ , $V_O = 200 \text{ mVp-p}$ , 10% to 90% $T_A = 25^\circ\text{C}$		2.4		ns	ns			
		$G = 2$ , $V_O = 2 \text{ Vp-p}$ , 10% to 90% $T_A = 25^\circ\text{C}$		8						
	Settling time	$V_S = 5 \text{ V}$ , $G = 2$ , 2-V output step, 0.1% $T_A = 25^\circ\text{C}$		30		ns	ns			
		$V_S = 5 \text{ V}$ , $G = 2$ , 2-V output step, 0.01% $T_A = 25^\circ\text{C}$		120						
Overload recovery time		$V_I \times G = V_S$ , $T_A = 25^\circ\text{C}$		8		ns				

## Electrical Characteristics (continued)

$V_S$  = 2.7 V to 5.5 V (single-supply). At  $T_A$  = 25°C,  $R_F$  = 604 Ω,  $R_L$  = 150 Ω, and connected to  $V_S / 2$ , (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Harmonic distortion	$G = 2, f = 1 \text{ MHz}, V_O = 2 \text{ Vp-p}, R_L = 200 \Omega$ $T_A = 25^\circ\text{C}$ (second harmonic)		-81		dBc
	$G = 2, f = 1 \text{ MHz}, V_O = 2 \text{ Vp-p}, R_L = 200 \Omega$ $T_A = 25^\circ\text{C}$ (third harmonic)		-93		dBc
Differential gain error	NTSC, $R_L = 150 \Omega, T_A = 25^\circ\text{C}$		0.02%		
Differential phase error	NTSC, $R_L = 150 \Omega, T_A = 25^\circ\text{C}$		0.05		°
<b>OUTPUT</b>					
Voltage output swing from rail	$V_S = 5 \text{ V}, R_L = 150 \Omega, A_{OL} > 84 \text{ dB}$		0.2	0.3	V
	$V_S = 5 \text{ V}, R_L = 1 \text{ k}\Omega$		0.1		V
$I_O$	Output current (continuous) ( <sup>1</sup> )		±60		mA
	$V_S = 5 \text{ V}, T_A = 25^\circ\text{C}$		±100		mA
	$V_S = 3 \text{ V}, T_A = 25^\circ\text{C}$		±80		
Closed-loop output impedance	$f < 100 \text{ kHz}$		0.02		Ω
<b>POWER SUPPLY</b>					
$V_S$	Specified voltage range	$T_A = 25^\circ\text{C}$	2.7	5.5	V
	Operating voltage range	$T_A = 25^\circ\text{C}$	2.5 to 5.5		V
$I_Q$	Quiescent current (per amplifier)	$V_S = 5 \text{ V}, \text{enabled}; I_O = 0$	8.3	11	mA
		$T_A = -40^\circ\text{C} \text{ to } +125^\circ\text{C}$		14	
<b>SHUTDOWN</b>					
Logic-LOW threshold <sup>(2)</sup> (disabled)	$T_A = 25^\circ\text{C}$			0.8	V
Logic-HIGH threshold <sup>(2)</sup> (enabled)	$T_A = 25^\circ\text{C}$		2		V
Enable time	$T_A = 25^\circ\text{C}$		100		ns
Disable time	$T_A = 25^\circ\text{C}$		30		ns
Shutdown current (per amplifier)	$V_S = 5 \text{ V}, \text{disabled}, T_A = 25^\circ\text{C}$		3.4		μA
<b>THERMAL SHUTDOWN</b>					
Junction temperature	Shutdown, $T_A = 25^\circ\text{C}$		160		°C
	Reset from shutdown, $T_A = 25^\circ\text{C}$		140		°C
Specified range	$T_A = 25^\circ\text{C}$		-40	125	°C
Operating range	$T_A = 25^\circ\text{C}$		-55	150	°C
Storage range	$T_A = 25^\circ\text{C}$		-65	150	°C

(1) See the *Output Voltage Swing vs Output Current* (图 21 and 图 23) in the *Typical Characteristics* section.

(2) Logic LOW and HIGH levels are CMOS logic compatible. They are referenced to  $V_-$ .

## 7.6 Typical Characteristics

$T_A = 25^\circ\text{C}$ ,  $V_S = 5 \text{ V}$ ,  $G = 2$ ,  $R_F = 604 \Omega$ , and  $R_L = 150 \Omega$  connected to  $V_S / 2$ , (unless otherwise noted)

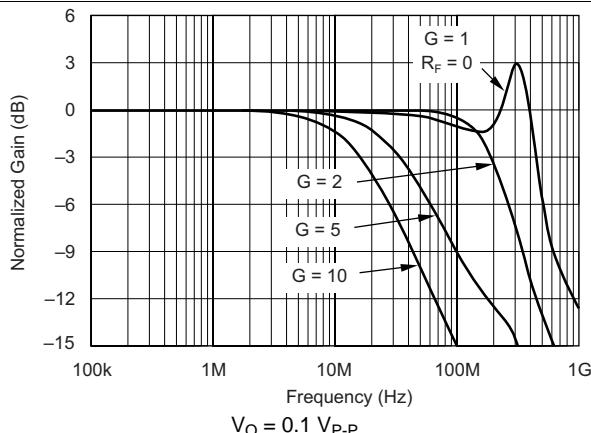


图 1. Noninverting Small-Signal Frequency Response

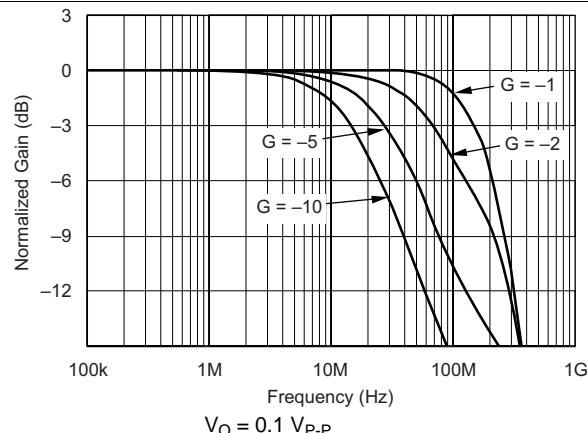


图 2. Inverting Small-Signal Frequency Response

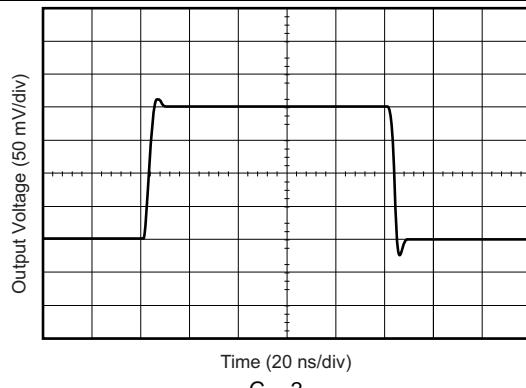


图 3. Noninverting Small-Signal Step Response

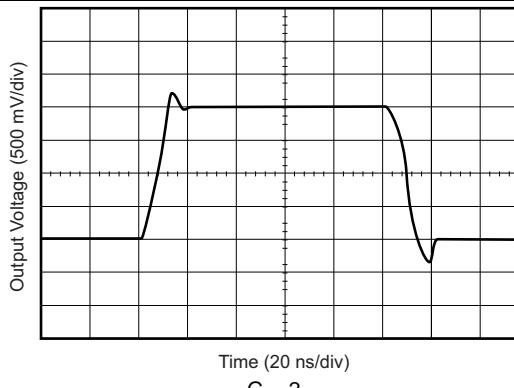


图 4. Noninverting Large-Signal Step Response

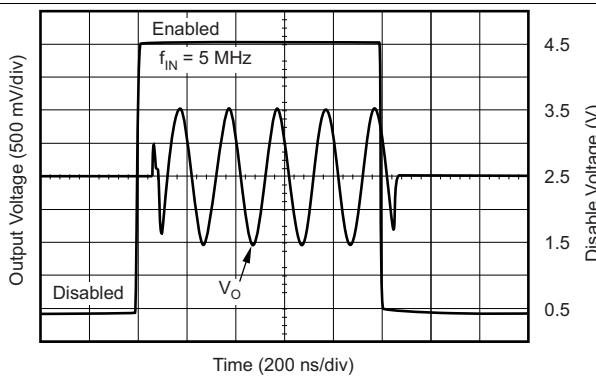


图 5. Large-Signal Disable and Enable Response

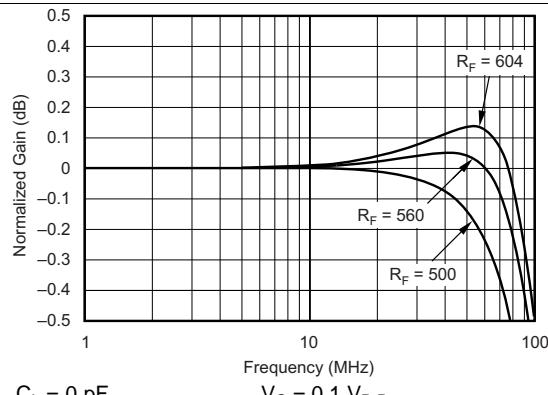


图 6. 0.1-dB Gain Flatness for Various  $R_F$  Values?

## Typical Characteristics (接下页)

$T_A = 25^\circ\text{C}$ ,  $V_S = 5 \text{ V}$ ,  $G = 2$ ,  $R_F = 604 \Omega$ , and  $R_L = 150 \Omega$  connected to  $V_S / 2$ , (unless otherwise noted)

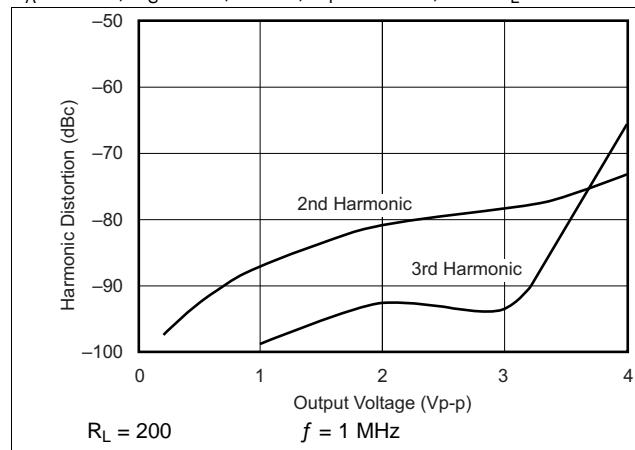


图 7. Harmonic Distortion vs Output Voltage

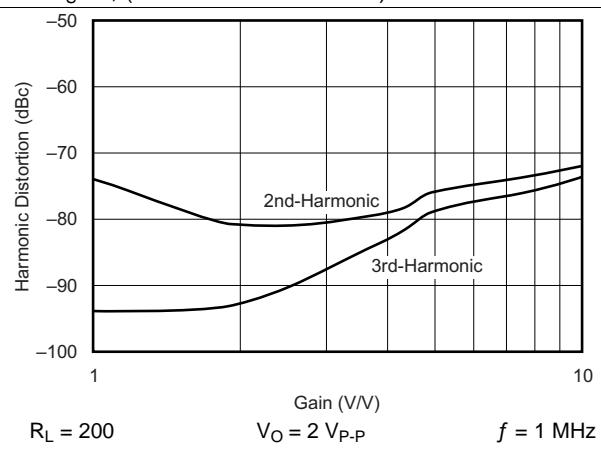


图 8. Harmonic Distortion vs Noninverting Gain

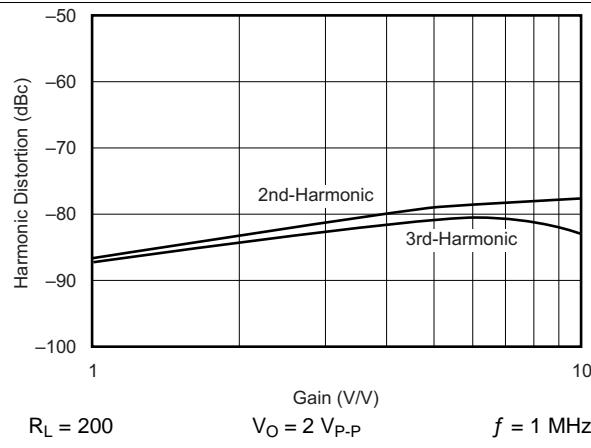


图 9. Harmonic Distortion vs Inverting Gain

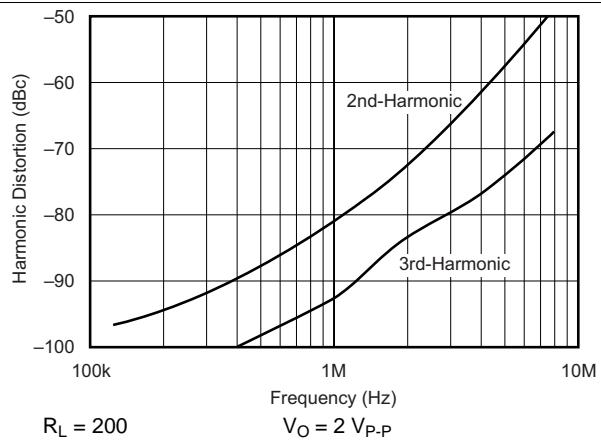


图 10. Harmonic Distortion vs Frequency

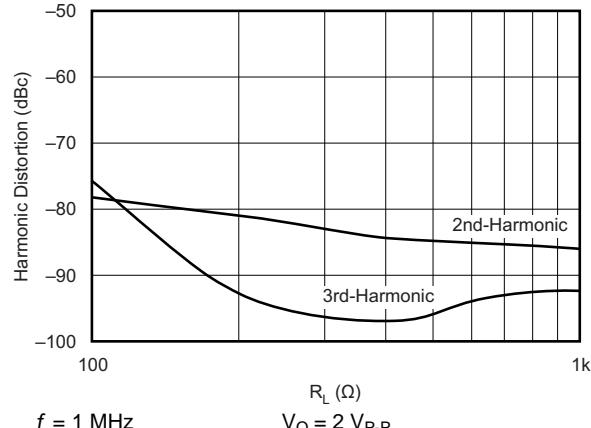


图 11. Harmonic Distortion vs Load Resistance

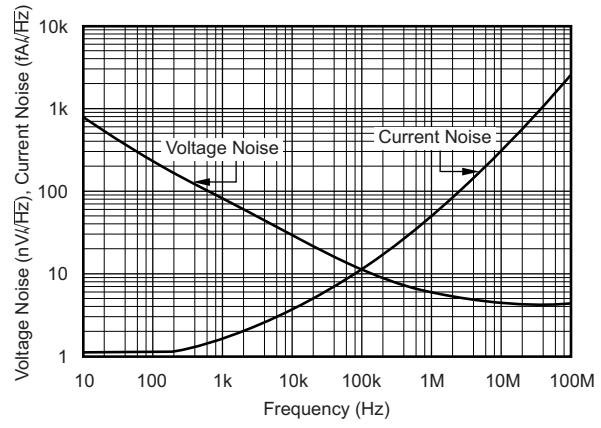


图 12. Input Voltage and Current Noise Spectral Density vs Frequency

## Typical Characteristics (接下页)

$T_A = 25^\circ\text{C}$ ,  $V_S = 5 \text{ V}$ ,  $G = 2$ ,  $R_F = 604 \Omega$ , and  $R_L = 150 \Omega$  connected to  $V_S / 2$ , (unless otherwise noted)

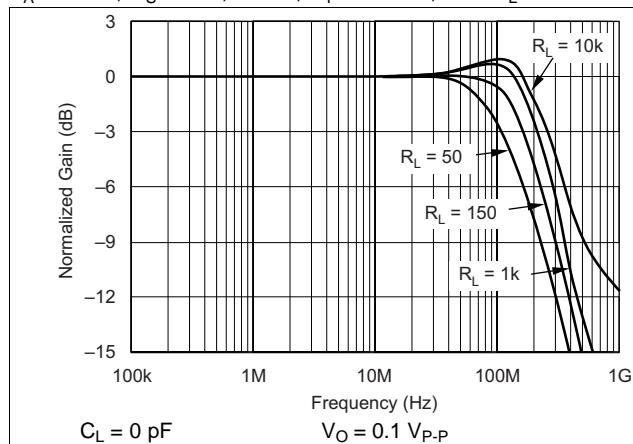


图 13. Frequency Response for Various  $R_L$  Values

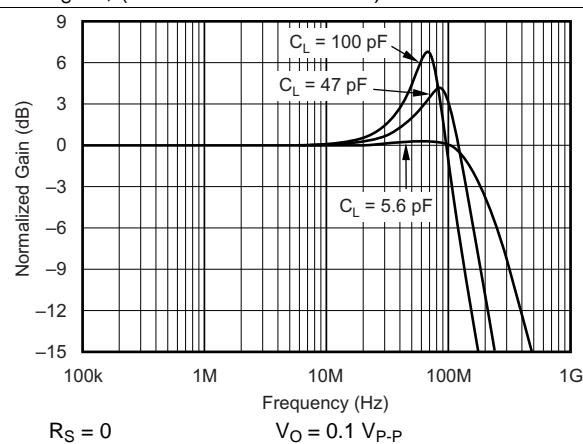


图 14. Frequency Response for Various  $C_L$  Values?

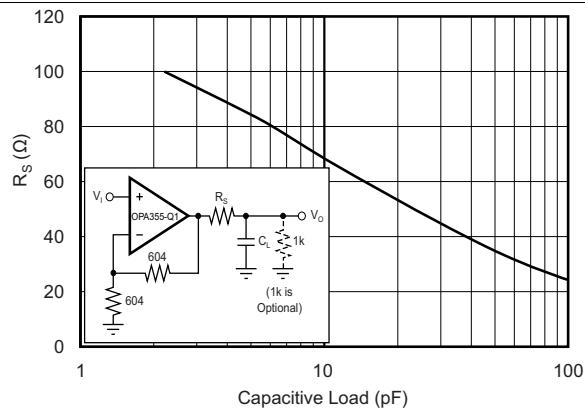


图 15. Recommended  $R_S$  Values vs Capacitive Load

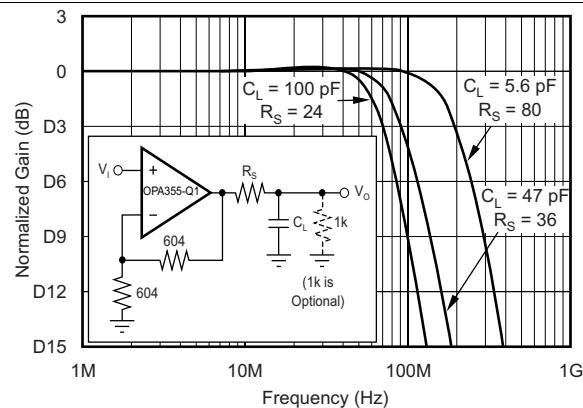


图 16. Frequency Response vs Capacitive Load

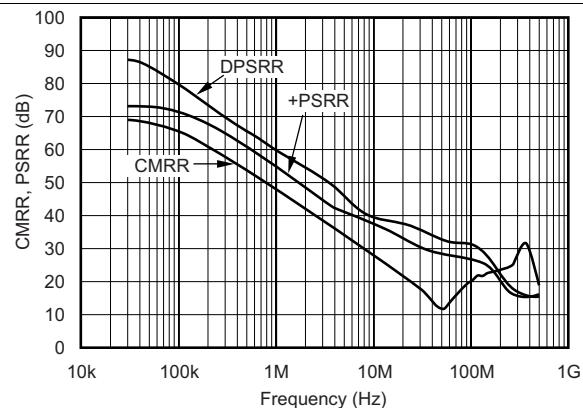


图 17. Common-Mode Rejection Ratio and Power-Supply Rejection Ratio vs Frequency

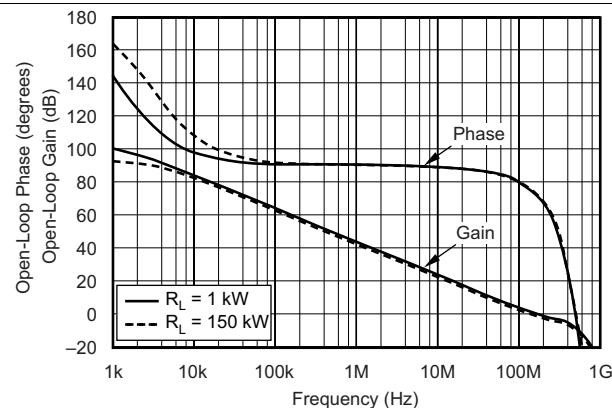


图 18. Open-Loop Gain and Phase

## Typical Characteristics (接下页)

$T_A = 25^\circ\text{C}$ ,  $V_S = 5 \text{ V}$ ,  $G = 2$ ,  $R_F = 604 \Omega$ , and  $R_L = 150 \Omega$  connected to  $V_S / 2$ , (unless otherwise noted)

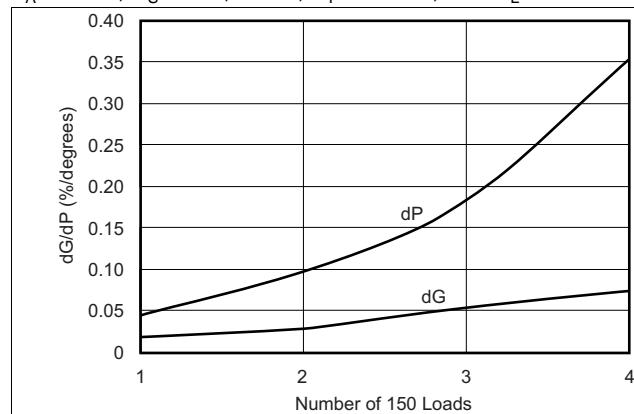


图 19. Composite Video Differential Gain and Phase

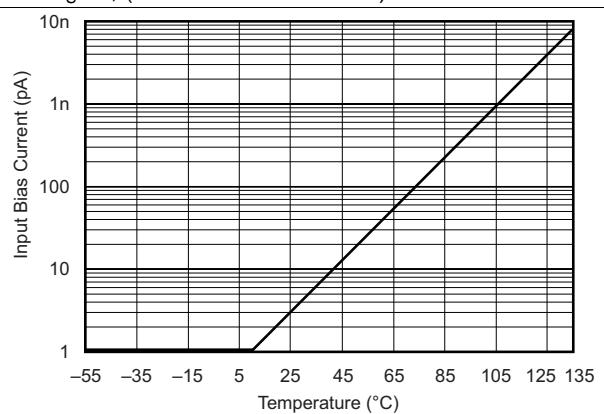


图 20. Input Bias Current vs Temperature

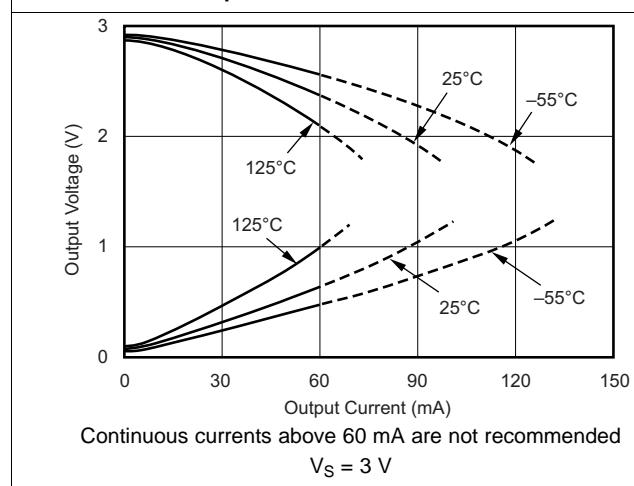


图 21. Output Voltage Swing vs Output Current

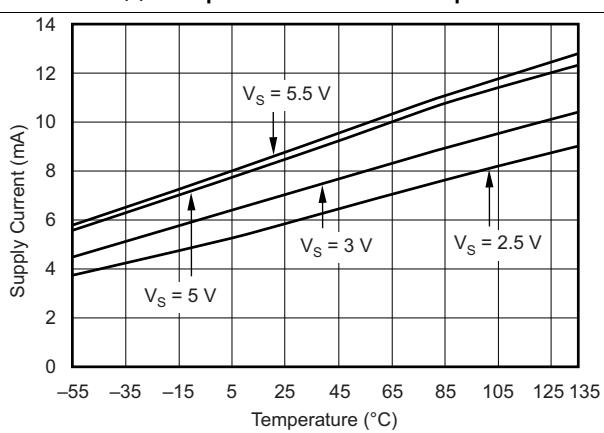


图 22. Supply Current vs Temperature

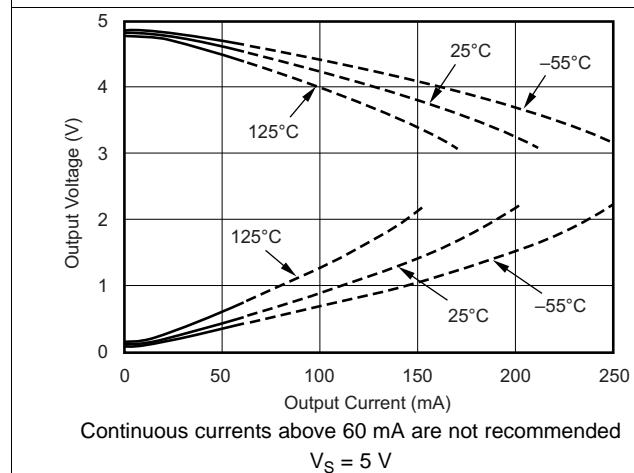


图 23. Output Voltage Swing vs Output Current

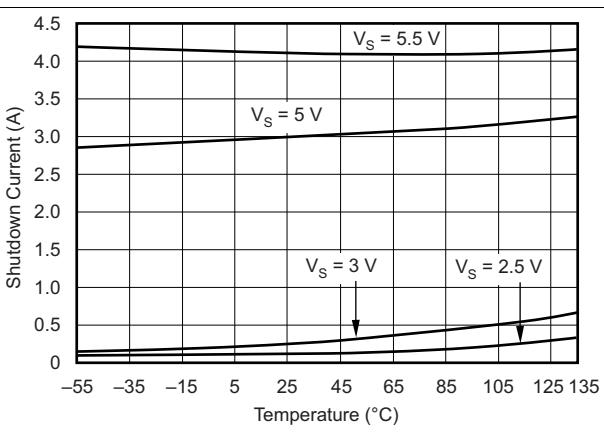


图 24. Shutdown Current vs Temperature

## Typical Characteristics (接下页)

$T_A = 25^\circ\text{C}$ ,  $V_S = 5 \text{ V}$ ,  $G = 2$ ,  $R_F = 604 \Omega$ , and  $R_L = 150 \Omega$  connected to  $V_S / 2$ , (unless otherwise noted)

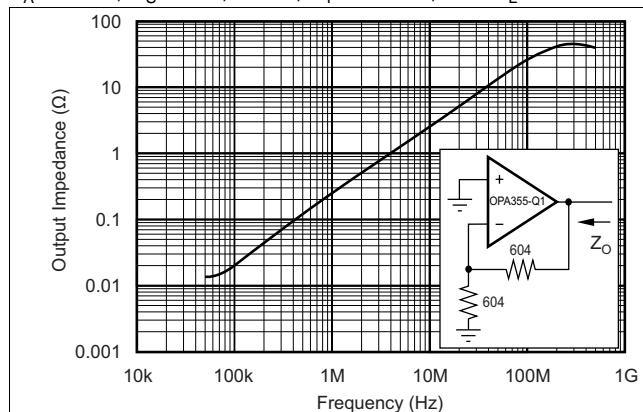
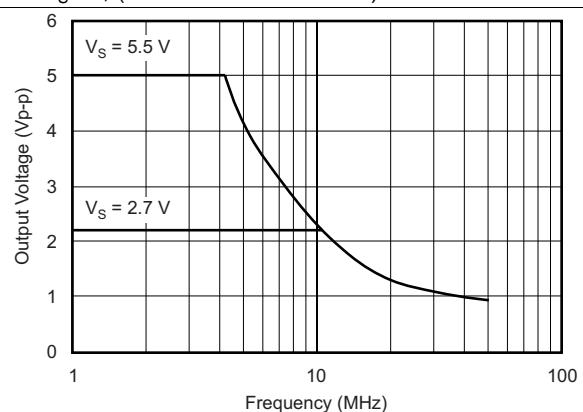


图 25. Closed-Loop Output Impedance vs Frequency



Maximum output voltage without slew-rate induced distortion

图 26. Maximum Output Voltage vs Frequency

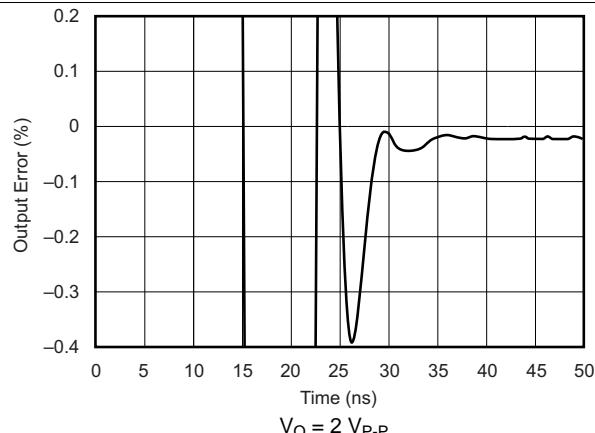


图 27. Output Settling Time to 0.1%

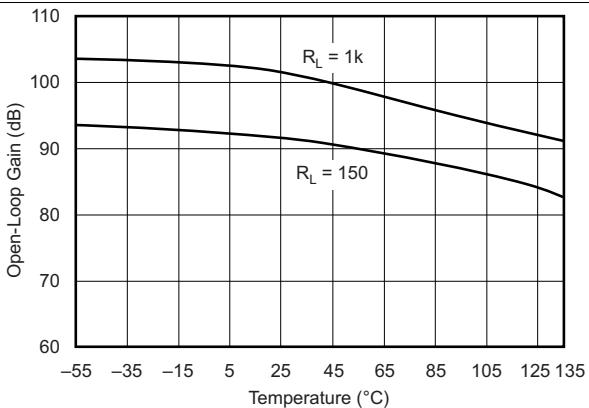


图 28. Open-Loop Gain vs Temperature

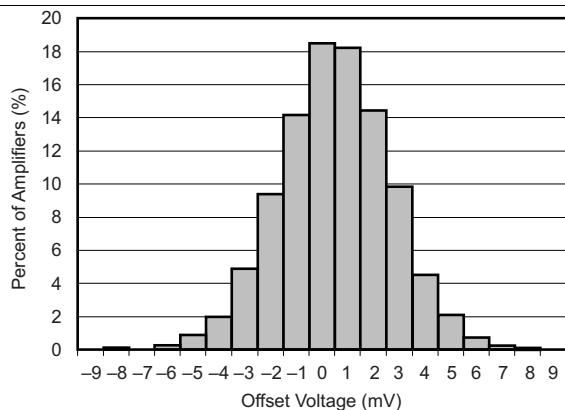


图 29. Offset Voltage Production Distribution

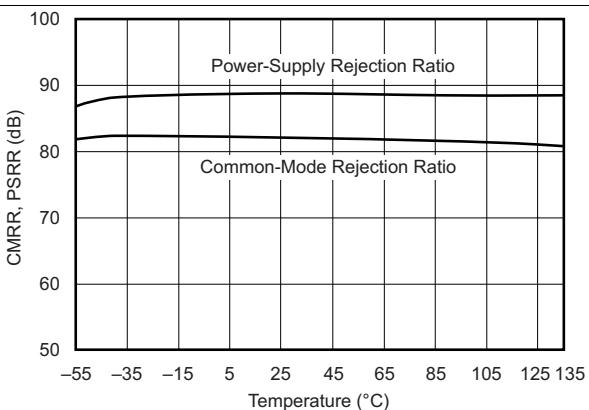


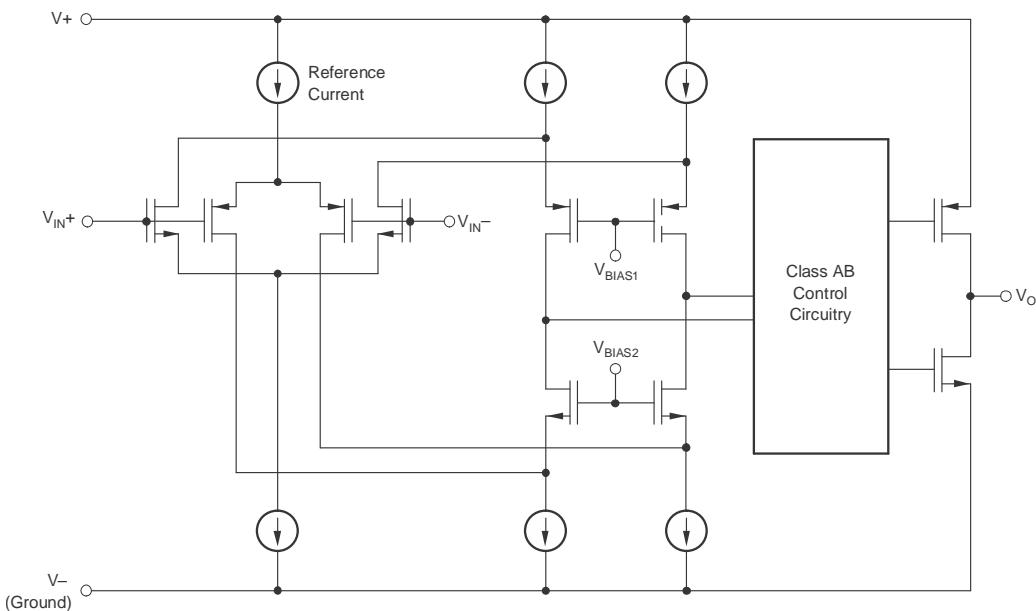
图 30. Common-Mode Rejection Ratio and Power-Supply Rejection Ratio vs Temperature

## 8 Detailed Description

### 8.1 Overview

The OPA355-Q1 operational amplifier is a high-speed, 300-V/ $\mu$ s, amplifier, making the device a great option for transimpedance applications. The device is unity-gain stable and can operate on a single-supply voltage (2.7 V to 5.5 V), or a split-supply voltage ( $\pm$ 1.35 V to  $\pm$ 2.75 V), making the device highly versatile and simple to use. The OPA355-Q1 amplifier is specified from 2.7 V to 5.5 V and over the automotive temperature range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .

### 8.2 Functional Block Diagram



### 8.3 Feature Description

#### 8.3.1 Operating Voltage

The OPA355-Q1 device is specified over a power-supply range of 2.7 V to 5.5 V ( $\pm$ 1.35 to  $\pm$ 2.75 V). However, the supply voltage ranges from 2.5 to 5.5 V ( $\pm$ 1.25 to  $\pm$ 2.75 V). Supply voltages higher than 7.5 V (absolute maximum) can permanently damage the amplifier.

Parameters that vary significantly over supply voltage or temperature are shown in the [Typical Characteristics](#) section of this data sheet.

#### 8.3.2 Enable Function

The OPA355-Q1 device is enabled by applying a TTL high-voltage level to the enable pin. Conversely, a TTL low-voltage level disables the amplifier, which reduces the supply current from 8.3 mA to 3.4  $\mu$ A per amplifier. This pin voltage is referenced to a single-supply ground. When using a split-supply, such as  $\pm$ 2.5 V, the enable and disable voltage levels are referenced to  $V_-$ . For portable battery-operated applications, this feature is used to greatly reduce the average current and as a result, extend battery life.

The enable input is modeled as a CMOS input gate with a 100-k $\Omega$  pullup resistor to  $V_+$ . The enable pin assumes a logic high and the amplifier turns on if the enable pin is left open.

The enable time is 100 ns and the disable time is 30 ns, which allows the OPA355-Q1 device to operate as a gated amplifier, or to have the output multiplexed onto a common output bus. When disabled, the output assumes a high-impedance state.

## Feature Description (接下页)

### 8.3.3 Output Drive

The output stage supplies a high short-circuit current (typically over 200 mA). Therefore, an on-chip thermal shutdown circuit is provided to protect the OPA355-Q1 device from dangerously-high junction temperatures. At 160°C, the protection circuit shuts down the amplifier. Normal operation resumes when the junction temperature cools to below 140°C.

#### 注

Running a continuous DC current in excess of  $\pm 60$  mA is not recommended. See the *Output Voltage Swing vs Output Current* graphs ([图 21](#) and [图 22](#)) in the [Typical Characteristics](#) section.

## 8.4 Device Functional Modes

The OPA355-Q1 device is powered on when the supply is connected. The device can operate as a single supply operational amplifier or dual supply amplifier depending on the application. The device can also be used with asymmetrical supplies as long as the differential voltage (V<sub>-</sub> to V<sub>+</sub>) is at least 1.8 V and no greater than 5.5 V (example: V<sub>-</sub> set to -3.5 V and V<sub>+</sub> set to 1.5 V).

## 9 Application and Implementation

### 9.1 Application Information

The OPA355-Q1 device is a CMOS, high-speed, voltage-feedback, operational amplifier (op-amp) designed for general-purpose applications.

The amplifier features a 200-MHz gain bandwidth and 300-V/ $\mu$ s slew rate, but the device is unity-gain stable and operates as a 1-V/V voltage follower.

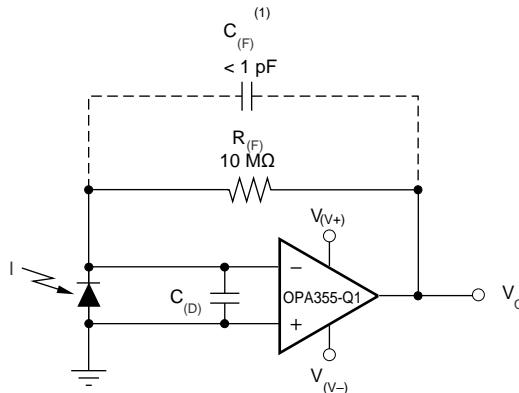
The input common-mode voltage range of the device includes ground, which allows the OPA355-Q1 to be used in virtually any single-supply application up to a supply voltage of 5.5 V.

### 9.2 Typical Applications

#### 9.2.1 Transimpedance Amplifier

Wide gain bandwidth, low input bias current, low input voltage, and current noise make the OPA355-Q1 device a preferred wideband photodiode transimpedance amplifier. Low-voltage noise is important because photodiode capacitance causes the effective noise gain of the circuit to increase at high frequency.

The key elements to a transimpedance design, as shown in [图 31](#), are the expected diode capacitance ( $C_{(D)}$ ), which must include the parasitic input common-mode and differential-mode input capacitance (4 pF + 5 pF), the desired transimpedance gain ( $R_{(FB)}$ ), and the gain-bandwidth (GBW) for the OPA355-Q1 device (20 MHz). With these three variables set, the feedback capacitor value ( $C_{(FB)}$ ) is set to control the frequency response.  $C_{(FB)}$  includes the stray capacitance of  $R_{(FB)}$ , which is 0.2 pF for a typical surface-mount resistor.



(1)  $C_{(FB)}$  is optional to prevent gain peaking.  $C_{(FB)}$  includes the stray capacitance of  $R_{(FB)}$ .

**图 31. Dual-Supply Transimpedance Amplifier**

##### 9.2.1.1 Design Requirements

PARAMETER	VALUE
Supply voltage $V_{(V+)}$	2.5 V
Supply voltage $V_{(V-)}$	-2.5 V

##### 9.2.1.2 Detailed Design Procedure

To achieve a maximally-flat, second-order Butterworth frequency response, the feedback pole must be set to:

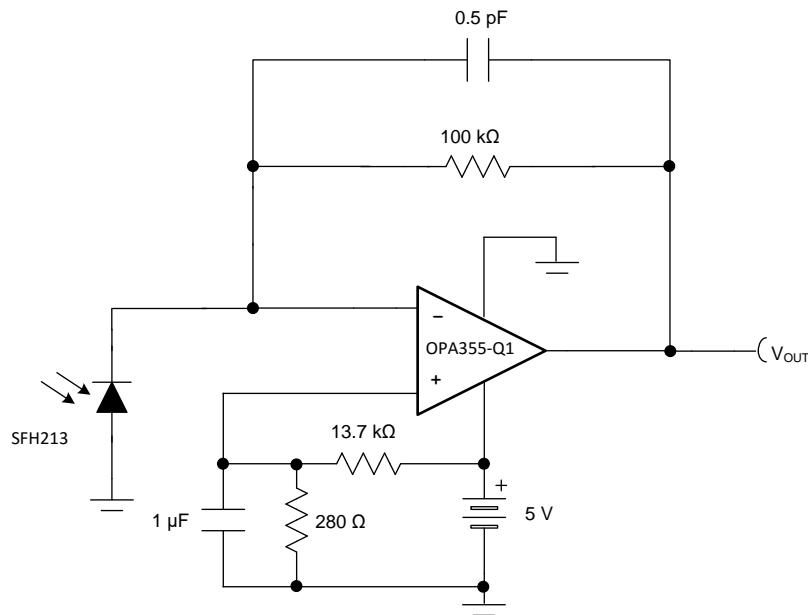
$$\frac{1}{2 \times \pi \times R_{(FB)} \times C_{(FB)}} = \sqrt{\frac{GBW}{4 \times \pi \times R_{(FB)} \times C_{(D)}}} \quad (1)$$

Use [公式 2](#) to calculate the bandwidth.

$$f_{(-3 \text{ dB})} = \sqrt{\frac{GBW}{2 \times \pi \times R_{(FB)} \times C_{(D)}}} \quad (2)$$

For other transimpedance bandwidths, consider the high-speed CMOS **OPA380** (90-MHz GBW), **OPA354** (100-MHz GBW), **OPA300** (180-MHz GBW), **OPA355** (200-MHz GBW), or **OPA656** and **OPA657** (400-MHz GBW).

For single-supply applications, the  $+IN_x$  input can be biased with a positive DC voltage to allow the output to reach true zero when the photodiode is not exposed to any light, and respond without the added delay that results from coming out of the negative rail; this configuration is shown in [图 32](#). This bias voltage appears across the photodiode, providing a reverse bias for faster operation.



**图 32. Single-Supply Transimpedance Amplifier**

For additional information, see the [Compensate Transimpedance Amplifiers Intuitively](#) application bulletin.

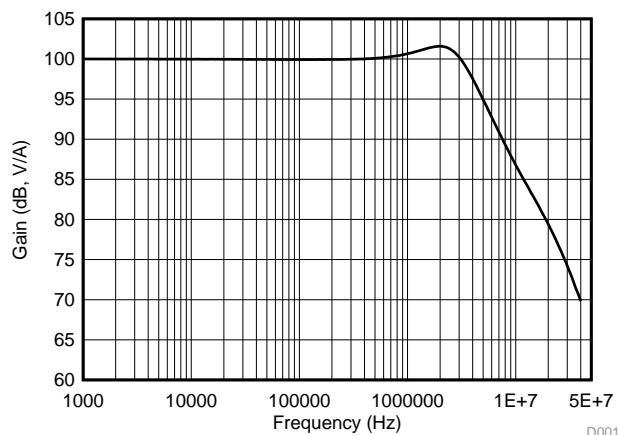
#### 9.2.1.2.1 Optimizing The Transimpedance Circuit

To achieve the best performance, select components according to the following guidelines:

1. For lowest noise, select  $R_{(FB)}$  to create the total required gain. Using a lower value for  $R_{(FB)}$  and adding gain after the transimpedance amplifier generally produces poorer noise performance. The noise produced by  $R_{(FB)}$  increases with the square-root of  $R_{(FB)}$ , whereas the signal increases linearly. Therefore, signal-to-noise ratio improves when all the required gain is placed in the transimpedance stage.
2. Minimize photodiode capacitance and stray capacitance at the summing junction (inverting input). This capacitance causes the voltage noise of the op amp to amplify (increasing amplification at high frequency). Using a low-noise voltage source to reverse-bias a photodiode can significantly reduce the capacitance. Smaller photodiodes have lower capacitance. Use optics to concentrate light on a small photodiode.
3. Noise increases with increased bandwidth. Limit the circuit bandwidth to only that required. Use a capacitor across the  $R_{(FB)}$  to limit bandwidth, even if not required for stability.
4. Circuit board leakage can degrade the performance of an otherwise well-designed amplifier. Clean the circuit board carefully. A circuit board guard trace that encircles the summing junction and is driven at the same voltage can help control leakage.

For additional information, see the [Noise Analysis of FET Transimpedance Amplifiers](#) and [Noise Analysis for High-Speed Op Amps](#) application bulletins).

### 9.2.1.3 Application Curve



-3 dB bandwidth is 4.56 MHz

图 33. AC Transfer Function

### 9.2.2 High-Impedance Sensor Interface

Many sensors have high source impedances that may range up to  $10 \text{ M}\Omega$ , or even higher. The output signal of sensors often must be amplified or otherwise conditioned by means of an amplifier. The input bias current of this amplifier can load the sensor output and cause a voltage drop across the source resistance, as shown in 图 34, where ( $V_{(+INx)} = V_S - I_{(BIAS)} \times R_{(S)}$ ). The last term,  $I_{(BIAS)} \times R_{(S)}$ , shows the voltage drop across  $R_{(S)}$ . To prevent errors introduced to the system as a result of this voltage, an op amp with very low input bias current must be used with high impedance sensors. This low current keeps the error contribution by  $I_{(BIAS)} \times R_{(S)}$  less than the input voltage noise of the amplifier, so that it does not become the dominant noise factor. The OPA355-Q1 op amp features very low input bias current (typically 200 fA), and is therefore a preferred choice for such applications.

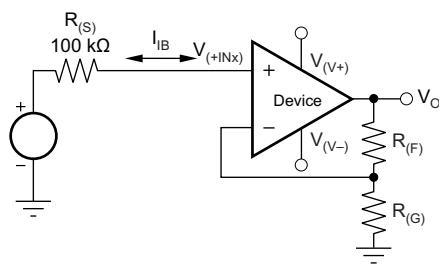
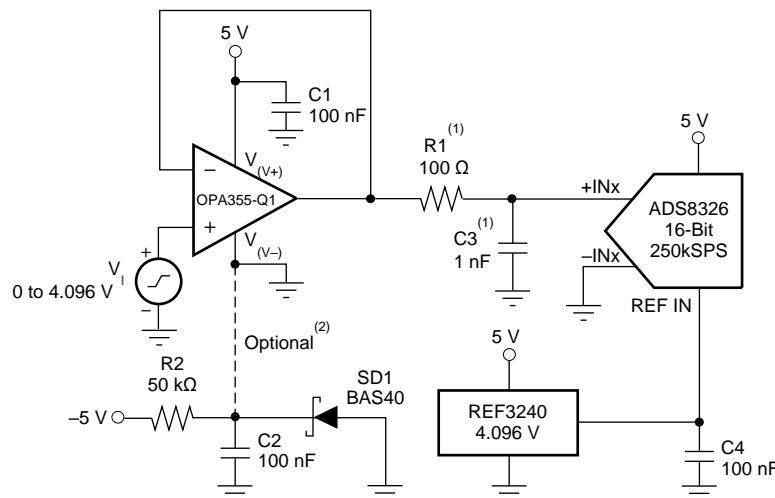


图 34. Noise as a Result of  $I_{(BIAS)}$

### 9.2.3 Driving ADCs

The OPA355-Q1 op amps are designed for driving sampling analog-to-digital converters (ADCs) with sampling speeds up to 1 MSPS. The zero-crossover distortion input stage topology allows the OPA355-Q1 device to drive ADCs without degradation of differential linearity and THD.

The OPA355-Q1 device can be used to buffer the ADC switched input capacitance and resulting charge injection while providing signal gain. [图 35](#) shows the OPA355-Q1 device configured to drive the [ADS8326](#).



(1) Suggested value; may require adjustment based on specific application.

(2) Single-supply applications lose a small number of ADC codes near ground as a result of op amp output swing limitation. If a negative power supply is available, this simple circuit creates a -0.3-V supply to allow output swing to true ground potential.

**图 35. Driving the ADS8326**

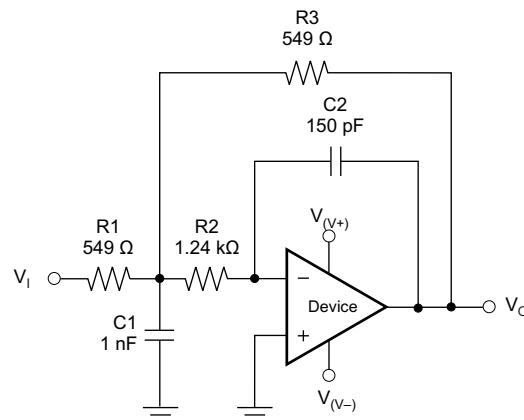
### 9.2.4 Active Filter

The OPA355-Q1 device is designed for active filter applications that require a wide bandwidth, fast slew rate, low-noise, single-supply operational amplifier. [图 36](#) shows a 500 kHz, second-order, low-pass filter using the multiple-feedback (MFB) topology. The components are selected to provide a maximally-flat Butterworth response. Beyond the cutoff frequency, roll-off is -40 dB/dec. The Butterworth response is preferred for applications requiring predictable gain characteristics, such as the anti-aliasing filter used in front of an ADC.

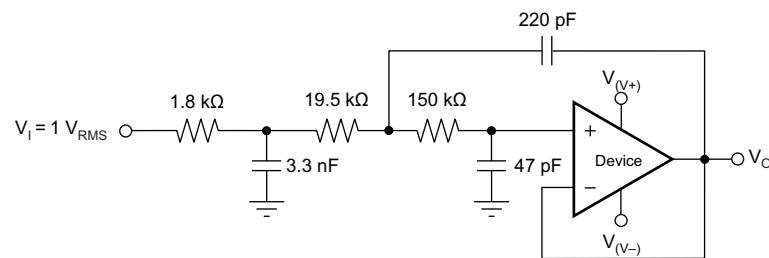
One point to observe when considering the MFB filter is that the output is inverted, relative to the input. If this inversion is not required, or not desired, a noninverting output can be achieved through one of the following options:

1. Adding an inverting amplifier
2. Adding an additional second-order MFB stage
3. Using a noninverting filter topology, such as the Sallen-Key (see [图 37](#)).

MFB and Sallen-Key, low-pass and high-pass filter synthesis is quickly accomplished using TI's [FilterPro™](#) program. This software is available as a free download at [www.ti.com](http://www.ti.com).



**图 36. Second-Order Butterworth 500-kHz Low-Pass Filter**



**图 37. OPA355-Q1 Configured as a Three-Pole, 20-kHz, Sallen-Key Filter**

## 10 Power Supply Recommendations

The OPA355-Q1 device is specified for operation from 2.7 to 5.5 V ( $\pm 1.35$  to  $\pm 2.75$  V); many specifications apply from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . Parameters that can exhibit significant variance with regard to operating voltage or temperature are shown in the *Typical Characteristics* section.

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout Guidelines* section.

Power dissipation depends on power-supply voltage, signal and load conditions. With DC signals, power dissipation is equal to the product of output current times the voltage across the conducting output transistor,  $\text{VS} - \text{VO}$ . Minimize power dissipation by using the lowest possible power-supply voltage required to ensure the required output voltage swing.

For resistive loads, the maximum power dissipation occurs at a DC output voltage of one-half the power-supply voltage. Dissipation with AC signals is lower. Application bulletin AB-039, *Power Amplifier Stress and Power Handling Limitations* explains how to calculate or measure power dissipation with unusual signals and loads, and is available on [www.ti.com](http://www.ti.com).

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heat sink. For reliable operation, limit junction temperature to  $150^{\circ}\text{C}$  maximum. To estimate the margin of safety in a complete design, increase the ambient temperature to trigger the thermal protection at  $160^{\circ}\text{C}$ . The thermal protection must trigger more than  $35^{\circ}\text{C}$  above the maximum expected ambient condition of the application.

## 11 Layout

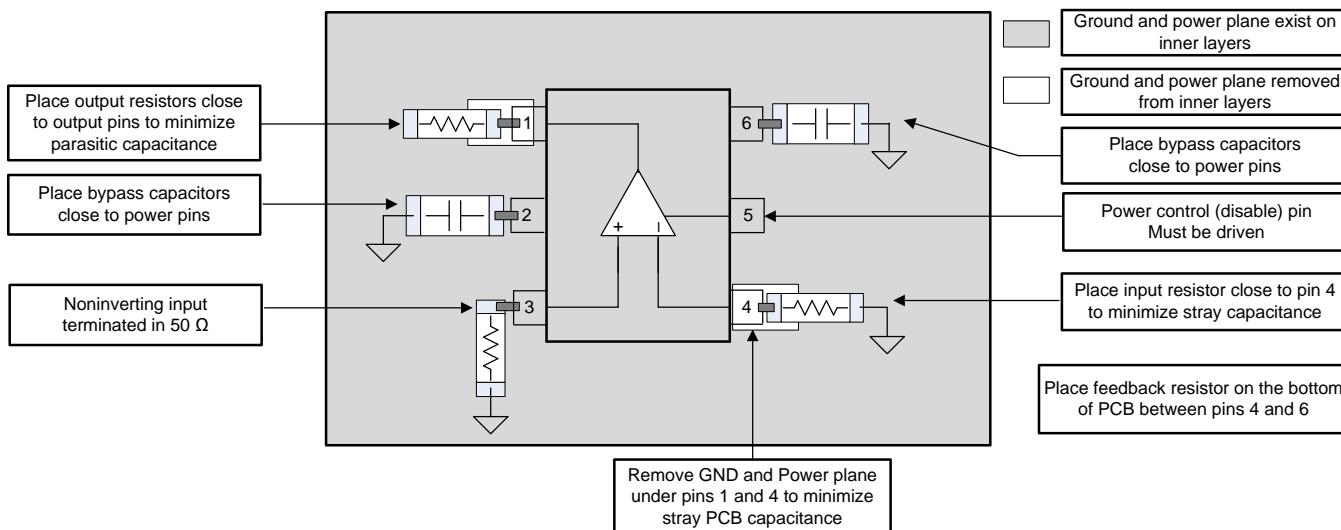
### 11.1 Layout Guidelines

Good high-frequency printed-circuit board (PCB) layout techniques must be used for the OPA355-Q1. Generous use of ground planes, short direct-signal traces, and a preferred bypass capacitor located at the V+ pin ensures clean and stable operation. Large areas of copper help dissipate heat generated within the amplifier in normal operation.

Sockets are not recommended for use with any high-speed amplifier.

A 10-nF ceramic bypass capacitor is the minimum recommended value; adding a 1- $\mu\text{F}$  or larger tantalum capacitor in parallel is beneficial when driving a low-resistance load. Providing adequate bypass capacitance is essential to achieving very low harmonic and intermodulation distortion.

### 11.2 Layout Example



**图 38. Layout Example**

## 12 器件和文档支持

### 12.1 商标

FilterPro is a trademark of Texas Instruments Incorporated.  
All other trademarks are the property of their respective owners.

### 12.2 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

### 12.3 术语表

[SLYZ022 — TI 术语表](#)。

这份术语表列出并解释术语、缩写和定义。

## 13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
OPA355QDBVRQ1	Active	Production	SOT-23 (DBV)   6	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SLN
OPA355QDBVRQ1.B	Active	Production	SOT-23 (DBV)   6	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SLN

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF OPA355-Q1 :**

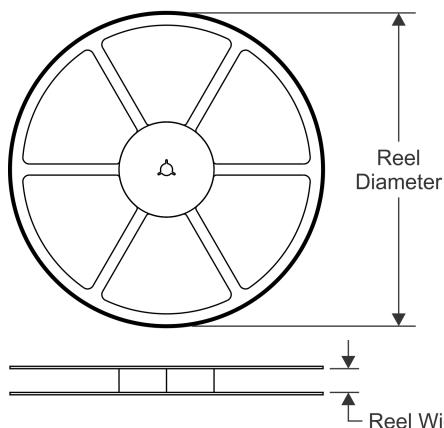
- Catalog : [OPA355](#)

NOTE: Qualified Version Definitions:

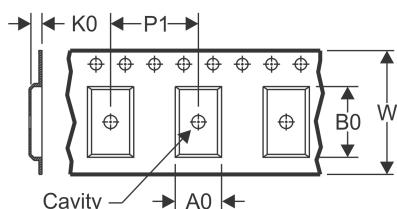
- Catalog - TI's standard catalog product

## TAPE AND REEL INFORMATION

### REEL DIMENSIONS

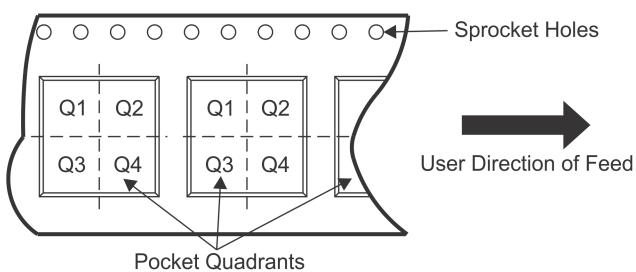


### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

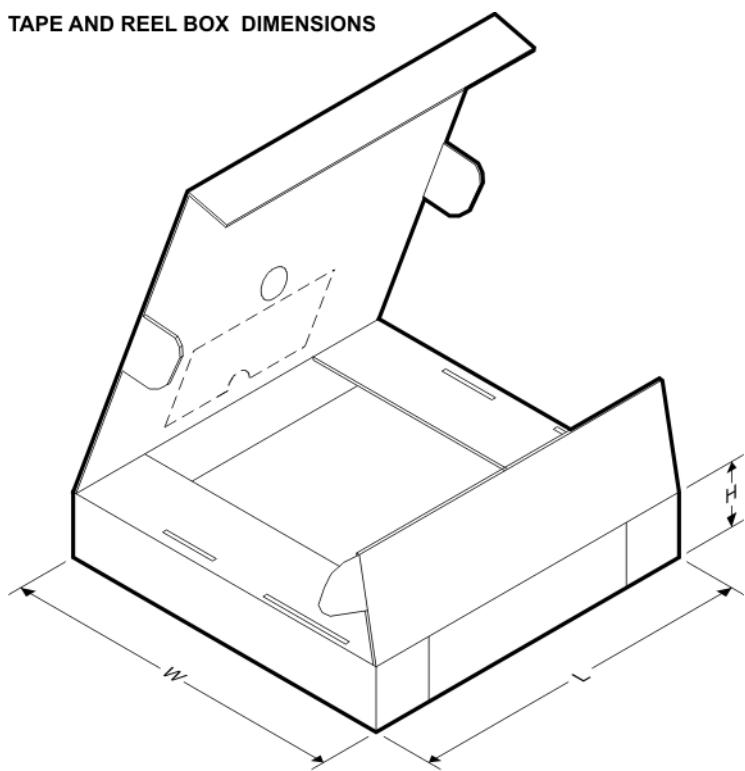
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA355QDBVRQ1	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA355QDBVRQ1	SOT-23	DBV	6	3000	445.0	220.0	345.0

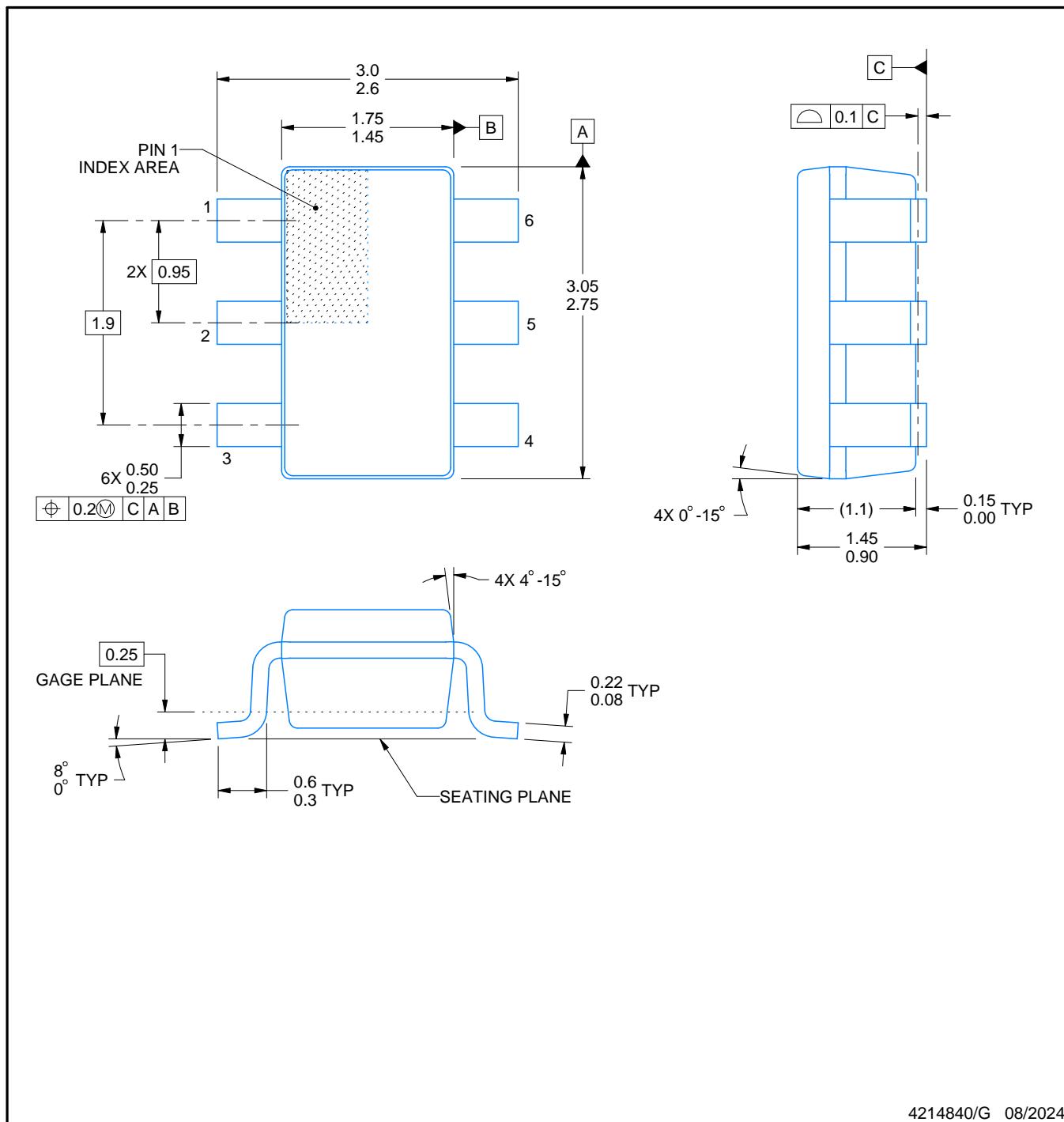
# PACKAGE OUTLINE

**DBV0006A**



**SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



## NOTES:

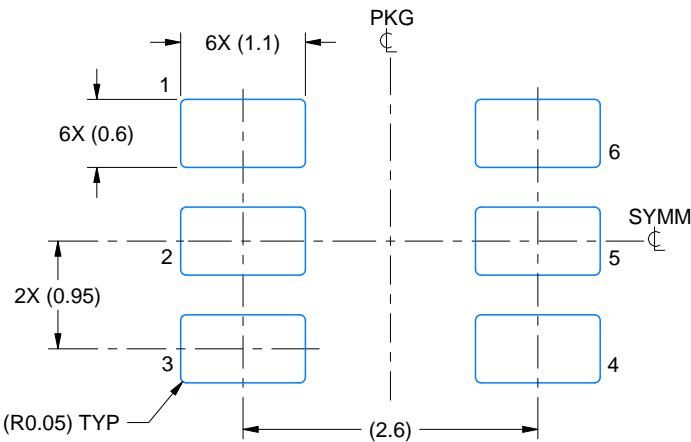
- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
- Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Reference JEDEC MO-178.

# EXAMPLE BOARD LAYOUT

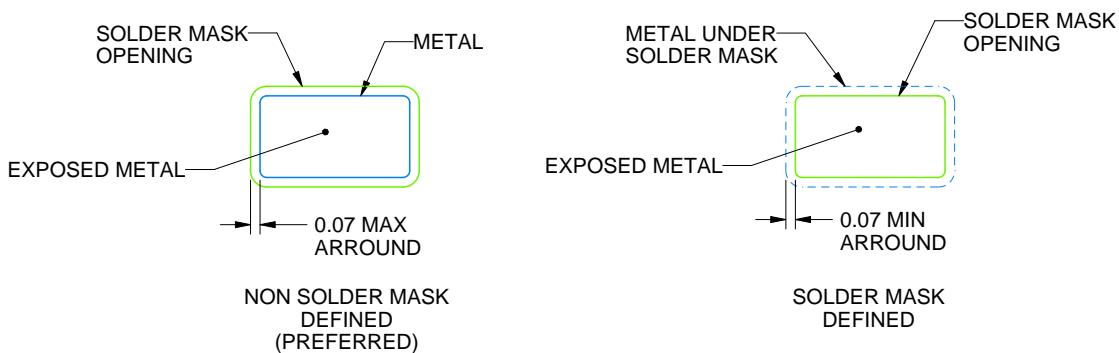
DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

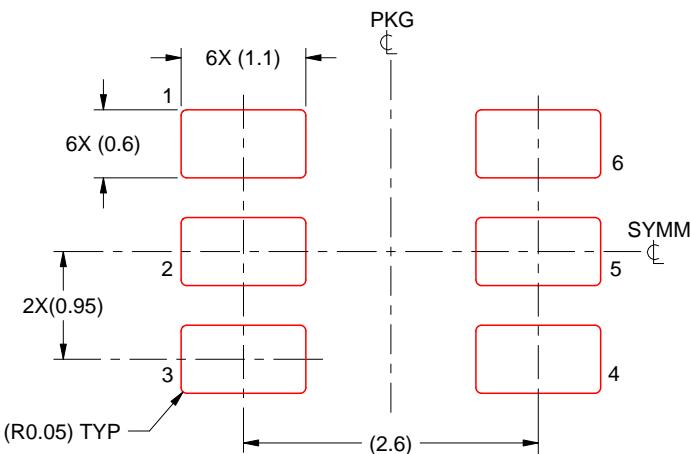
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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